Form PTO 1449 (Modified)		U.S. DEPARTMENT ( PATENT AND TRAD	ATTY DOCKET NO. 198092US-2S DIV				SERIAL NO.  New Divisional Application					
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LIST OF	REFE	RENCES CITED BY APP	Hironobu KON			ou KON	et al		94			
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\*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.